



# PSMN1R5-25MLH

N-channel 25 V, 1.81 mΩ, 150 A logic level MOSFET in LFAK33 using NextPowerS3 technology

30 September 2019

Product data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFAK33 package. NextPowerS3 technology delivers low  $R_{DSon}$ , low  $I_{DSS}$  leakage and high efficiency. Rated to 150 A and optimized with low gate resistance ( $R_G$ ) for fast-switching applications.

## 2. Features and benefits

- Optimized for low  $R_{DSon}$  and low gate resistance ( $R_G$ )
- Fast switching – reduced switching losses
- Strong linear-mode (SOA) rating
- Low leakage < 1  $\mu$ A at 25 °C
- Low spiking and ringing for low EMI designs
- Optimized for 4.5 V gate drive
- 150 A continuous  $I_{D(max)}$  rating
- High reliability copper-clip bonded and solder die attach LFAK33 package
- Qualified to 175 °C
- Exposed leads for optimal visual solder inspection

## 3. Applications

- Synchronous buck regulator
- Synchronous rectifier in AC-DC and DC-DC applications
- BLDC (brushless) motor control
- eFuse and battery protection
- OR-ing and hot-swap

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	25	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	[1]	-	150	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	106	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	1.46	1.81	mΩ
		$V_{GS} = 4.5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	2.1	2.7	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}$ ; $V_{DS} = 12\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	1	5.6	11.2	nC
$Q_{G(tot)}$	total gate charge		7.7	17	28	nC

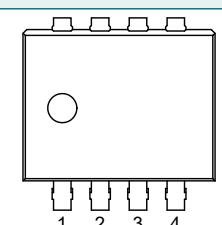
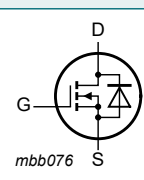
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
S	softness factor	$I_S = 25 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 12 \text{ V}$ ; <a href="#">Fig. 16</a>	-	0.88	-	

[1] 150A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK33 (SOT1210)</p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	Mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R5-25MLH	LFAK33	Plastic, single ended surface mounted package (LFAK33); 8 leads; 0.65 mm pitch	SOT1210

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R5-25MLH	1H525L

## 8. Limiting values

Table 5. Limiting values

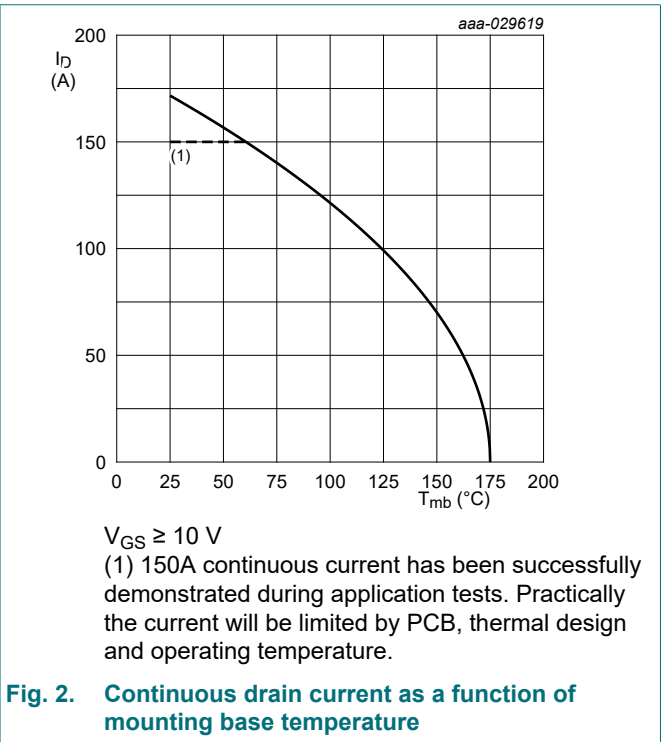
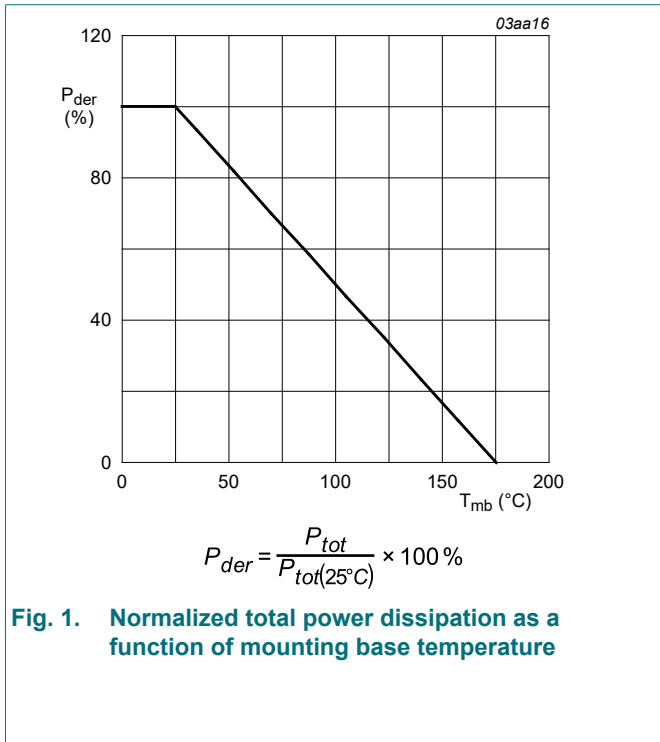
In accordance with the Absolute Maximum Rating System (IEC 60134).

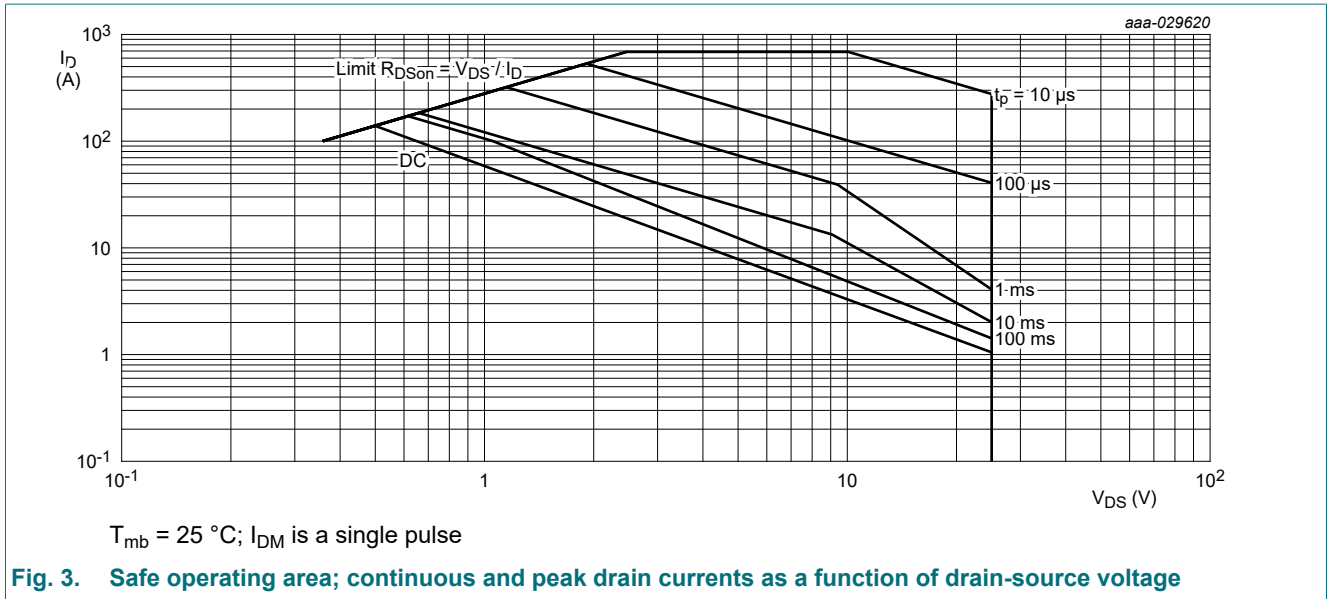
Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{DS}$	drain-source voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$	-	25	V	
$V_{DGR}$	drain-gate voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$ ; $R_{GS} = 20 \text{ k}\Omega$	-	25	V	
$V_{GS}$	gate-source voltage		-20	20	V	
$P_{tot}$	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>	-	106	W	
$I_D$	drain current	$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>	[1]	-	150	A
		$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 100 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>		-	121	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>	-	687	A	
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$	

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Symbol	Parameter	Conditions	Min	Max	Unit
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	106	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	687	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 25\text{ A}$ ; $V_{sup} \leq 25\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped; $t_p = 811\text{ }\mu\text{s}$	[2]	-	330 mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} \leq 25\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $R_{GS} = 50\text{ }\Omega$	[2]	-	87 A

- [1] 150A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test

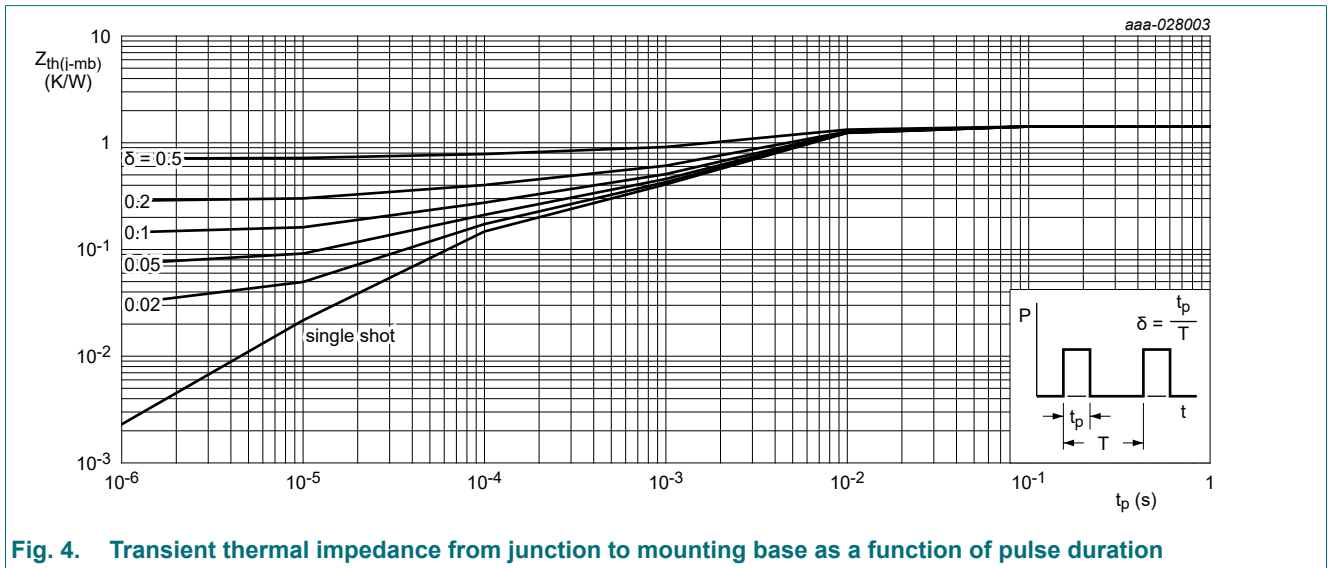




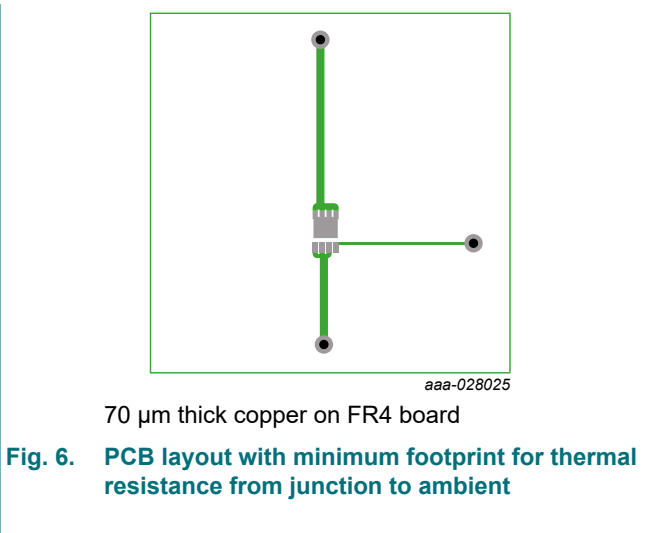
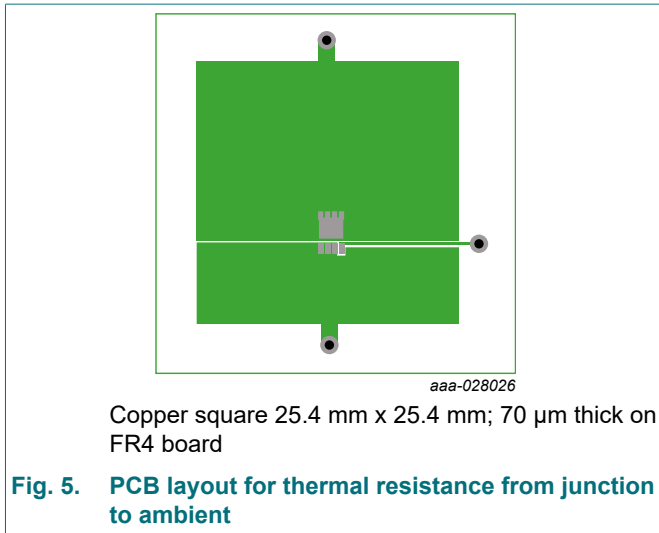
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	1.12	1.42	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W
		Fig. 6	-	130	-	K/W



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## 10. Characteristics

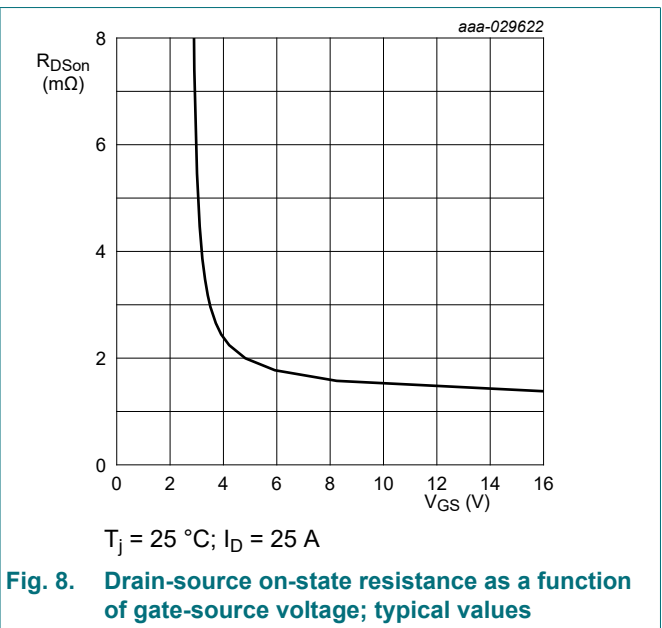
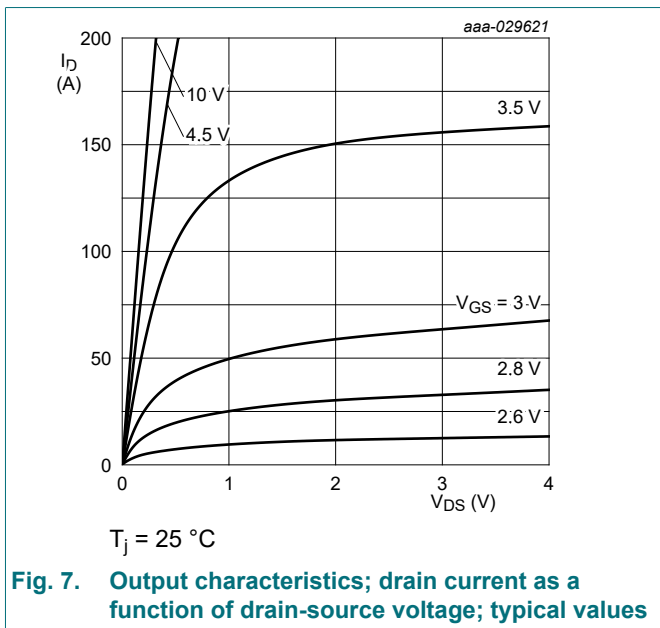
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	25	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.2	1.73	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	-4	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	2.5	-	μA
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	1.46	1.81	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	-	3.2	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	2.1	2.7	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	-	4.8	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	0.5	1.2	3	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	7.7	17	28	nC
		$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	15.8	35	58	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ C$	-	18	-	nC

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$Q_{GS}$	gate-source charge	$I_D = 25\text{ A}; V_{DS} = 12\text{ V}; V_{GS} = 4.5\text{ V};$ <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	1.5	5.5	10.5	nC	
$Q_{GS(th)}$	pre-threshold gate-source charge		0.86	3.2	6.1	nC	
$Q_{GS(th-pl)}$	post-threshold gate-source charge		0.6	2.2	4.2	nC	
$Q_{GD}$	gate-drain charge		1	5.6	11.2	nC	
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}; V_{DS} = 12\text{ V};$ <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	-	2.8	-	V	
$C_{iss}$	input capacitance	$V_{DS} = 12\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 14</a>	1267	2111	3167	pF	
$C_{oss}$	output capacitance		872	1454	2181	pF	
$C_{rss}$	reverse transfer capacitance		62	230	552	pF	
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\text{ V}; R_L = 0.4\text{ } \Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 5\text{ } \Omega$	-	14	-	ns	
$t_r$	rise time		-	25	-	ns	
$t_{d(off)}$	turn-off delay time		-	18	-	ns	
$t_f$	fall time		-	14	-	ns	
$Q_{oss}$	output charge	$V_{GS} = 0\text{ V}; V_{DS} = 12\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C}$	-	23	-	nC	
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>	-	0.78	1	V	
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 12\text{ V};$ <a href="#">Fig. 16</a>	-	30	-	ns	
$Q_r$	recovered charge		[1]	-	23	-	nC
$t_a$	reverse recovery rise time		-	16	-	ns	
$t_b$	reverse recovery fall time		-	14	-	ns	
S	softness factor		-	0.88	-		

[1] includes capacitive recovery



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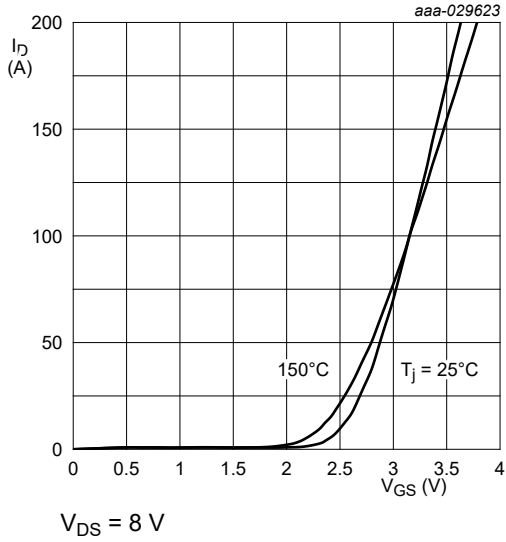


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

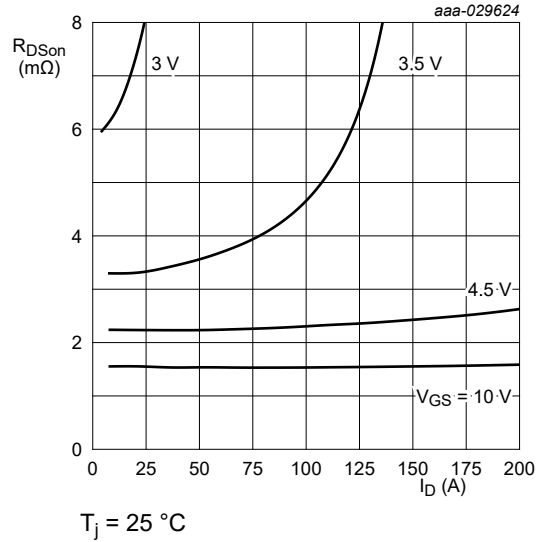


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

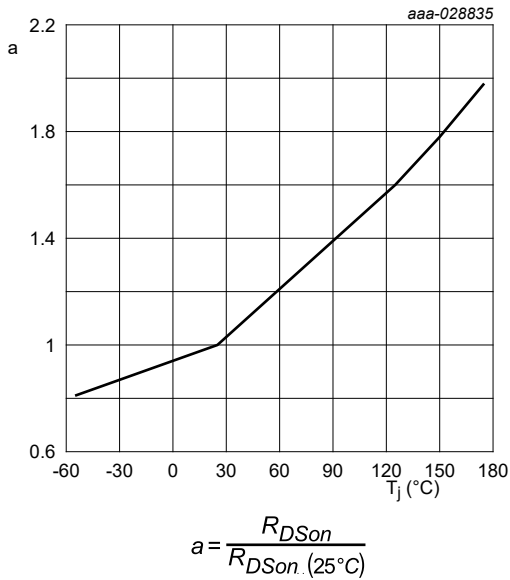


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

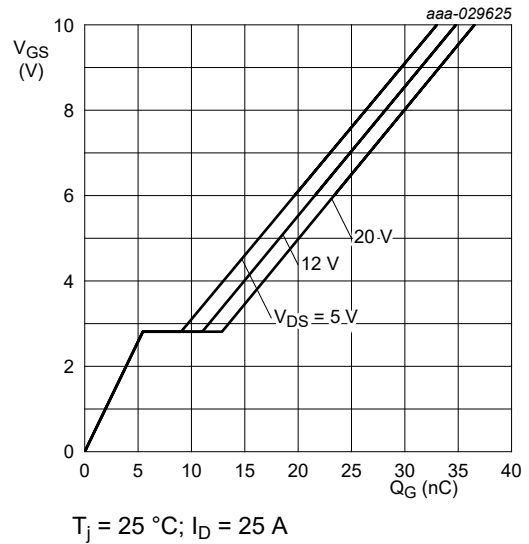


Fig. 12. Gate-source voltage as a function of gate charge; typical values

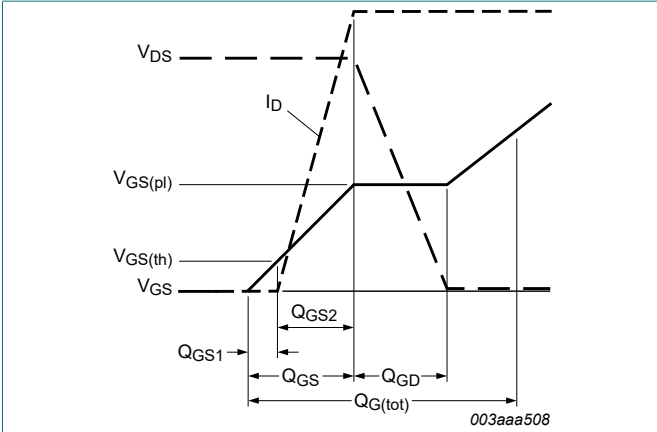


Fig. 13. Gate charge waveform definitions

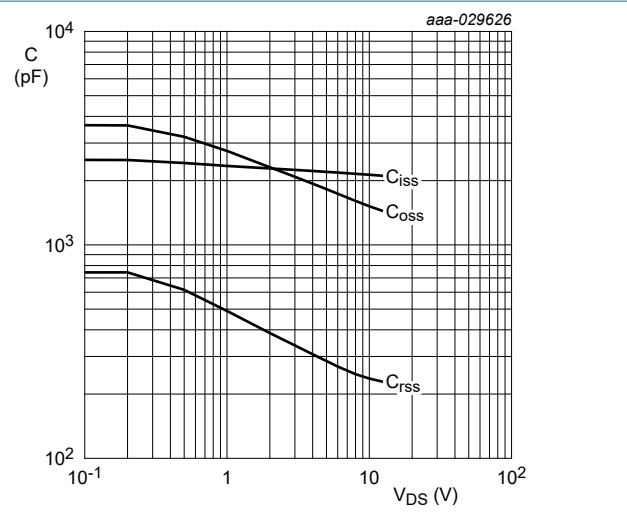


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values  
 $V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

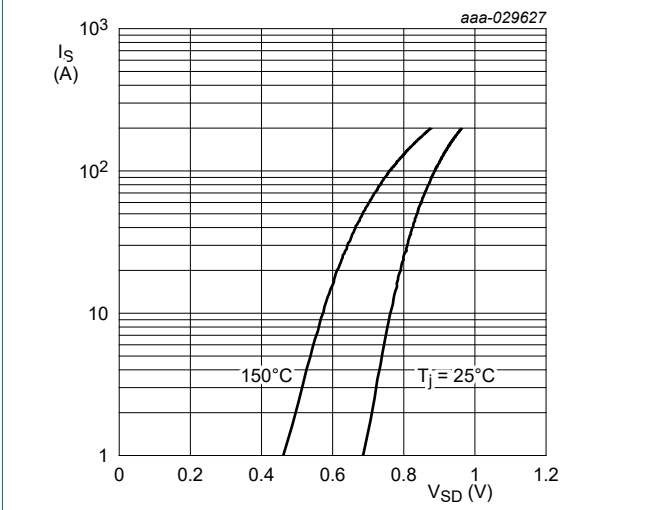


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values  
 $V_{GS} = 0 \text{ V}$

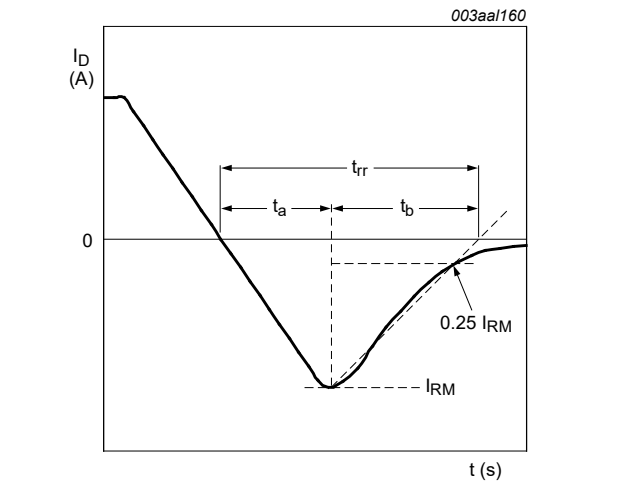


Fig. 16. Reverse recovery timing definition



### 11. Package outline

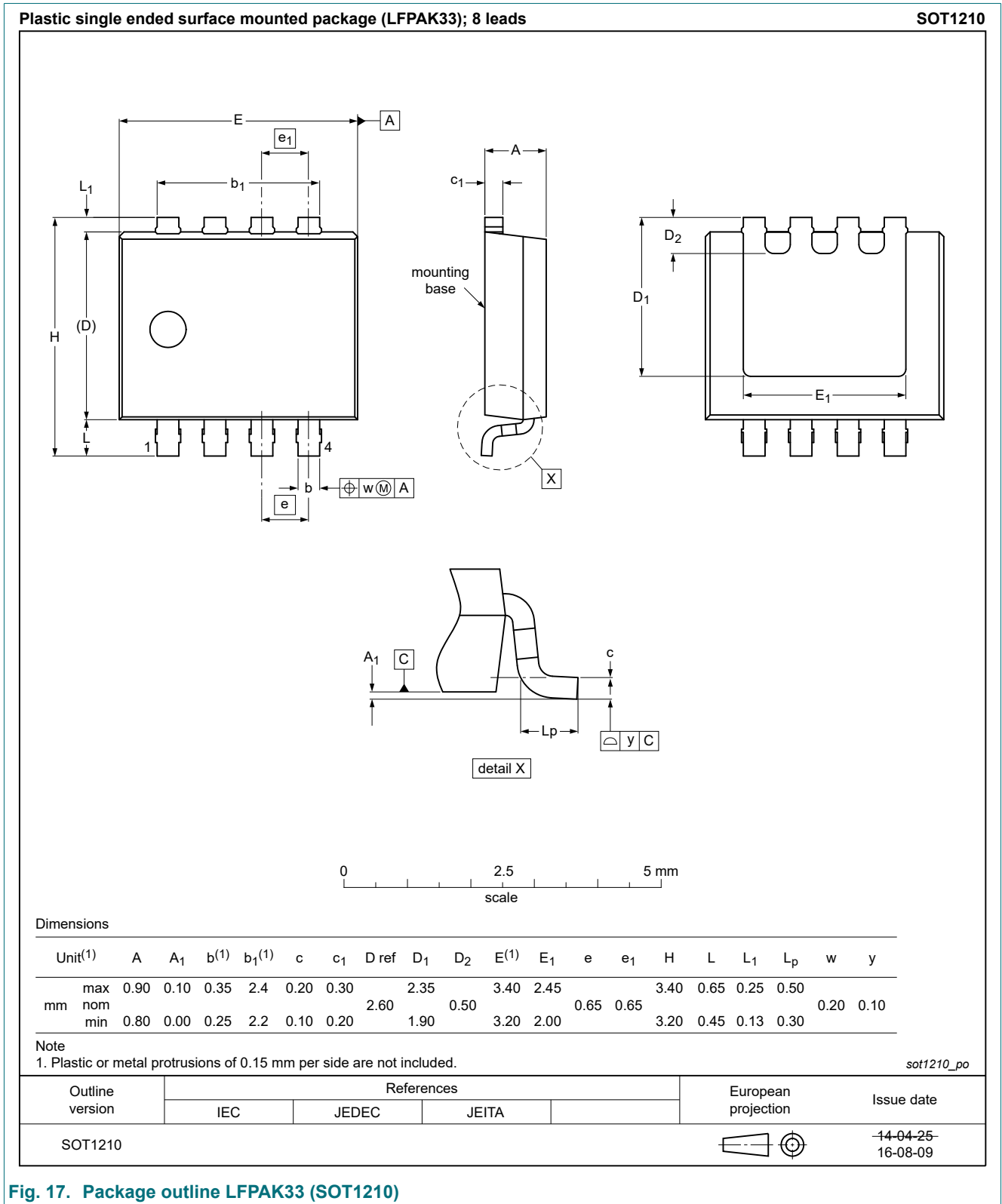
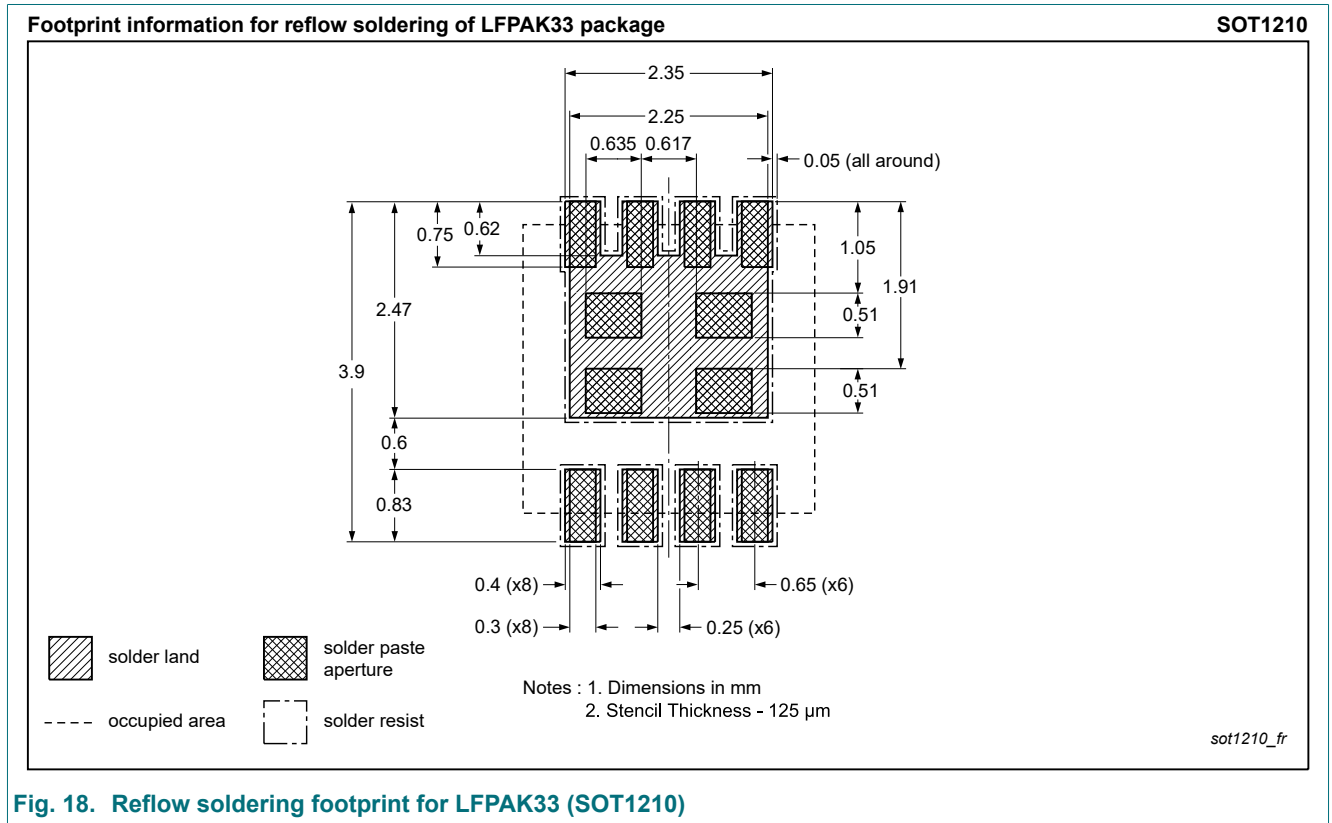


Fig. 17. Package outline LPAK33 (SOT1210)

## 12. Soldering



## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 30 September 2019

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